

## NCE N-Channel Enhancement Mode Power MOSFET

### DESCRIPTION

The NCE3080K uses advanced trench technology and design to provide excellent  $R_{DS(ON)}$  with low gate charge. It can be used in a wide variety of applications.

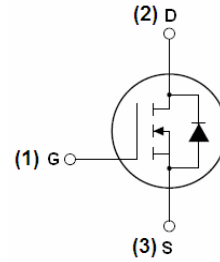
### GENERAL FEATURES

- $V_{DS} = 30V, I_D = 80A$   
 $R_{DS(ON)} < 6.5m\Omega @ V_{GS} = 10V$   
 $R_{DS(ON)} < 10m\Omega @ V_{GS} = 5V$
- High density cell design for ultra low  $R_{dson}$
- Fully characterized Avalanche voltage and current
- Good stability and uniformity with high  $E_{AS}$
- Excellent package for good heat dissipation
- Special process technology for high ESD capability

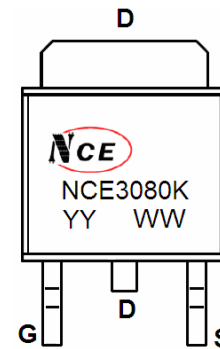
### Application

- Power switching application
- Hard Switched and High Frequency Circuits
- Uninterruptible Power Supply

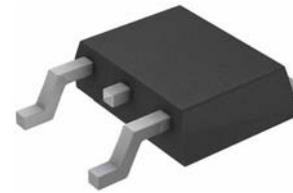
**100% UIS TESTED!**



Schematic diagram



Marking and pin Assignment



TO-252 top view

### Package Marking And Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
NCE3080K	NCE3080K	TO-252	-	-	-

### Absolute Maximum Ratings (TA=25°C unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	$V_{DS}$	30	V
Gate-Source Voltage	$V_{GS}$	$\pm 20$	V
Drain Current-Continuous	$I_D$	80	A
Drain Current-Continuous( $T_C = 100^\circ C$ )	$I_D(100^\circ C)$	50	A
Pulsed Drain Current	$I_{DM}$	170	A
Maximum Power Dissipation	$P_D$	83	W
Derating factor		0.56	W/°C
Single pulse avalanche energy (Note 5)	$E_{AS}$	140	mJ
Operating Junction and Storage Temperature Range	$T_J, T_{STG}$	-55 To 175	°C

## Thermal Characteristic

Thermal Resistance, Junction-to-Case(Note 2)	$R_{\theta JC}$	1.8	$^{\circ}\text{C/W}$
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## Electrical Characteristics (TA=25 $^{\circ}\text{C}$ unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
<b>Off Characteristics</b>						
Drain-Source Breakdown Voltage	$BV_{DSS}$	$V_{GS}=0V, I_D=250\mu A$	30			V
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS}=30V, V_{GS}=0V$			1	$\mu A$
Gate-Body Leakage Current	$I_{GSS}$	$V_{GS}=\pm 20V, V_{DS}=0V$			$\pm 100$	nA
<b>On Characteristics (Note 3)</b>						
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=250\mu A$	1		3	V
Drain-Source On-State Resistance	$R_{DS(on)}$	$V_{GS}=10V, I_D=30A$			6.5	m $\Omega$
		$V_{GS}=5V, I_D=24A$			10	
Forward Transconductance	$g_{FS}$	$V_{DS}=10V, I_D=24A$	20			S
<b>Dynamic Characteristics (Note4)</b>						
Input Capacitance	$C_{iss}$	$V_{DS}=15V, V_{GS}=0V,$ $F=1.0\text{MHz}$		4700		PF
Output Capacitance	$C_{oss}$			500		PF
Reverse Transfer Capacitance	$C_{rss}$			345		PF
<b>Switching Characteristics (Note 4)</b>						
Turn-on Delay Time	$t_{d(on)}$	$V_{DD}=10V, I_D=30A$ $V_{GS}=10V, R_{GEN}=2.7\Omega$		20		nS
Turn-on Rise Time	$t_r$			15		nS
Turn-Off Delay Time	$t_{d(off)}$			65		nS
Turn-Off Fall Time	$t_f$			10		nS
Total Gate Charge	$Q_g$	$V_{DS}=10V, I_D=30A,$ $V_{GS}=10V$		51		nC
Gate-Source Charge	$Q_{gs}$			14		nC
Gate-Drain Charge	$Q_{gd}$			11		nC
<b>Drain-Source Diode Characteristics</b>						
Diode Forward Voltage (Note 3)	$V_{SD}$	$V_{GS}=0V, I_S=24A$		0.85	1.2	V
Diode Forward Current (Note 2)	$I_S$				80	A
Reverse Recovery Time	$t_{rr}$	$T_J = 25^{\circ}\text{C}, I_F = 80A$ $di/dt = 100A/\mu s(\text{Note3})$		32	50	nS
Reverse Recovery Charge	$Q_{rr}$				12	20
Forward Turn-On Time	$t_{on}$	Intrinsic turn-on time is negligible (turn-on is dominated by LS+LD)				

## Notes:

1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. Surface Mounted on FR4 Board,  $t \leq 10$  sec.
3. Pulse Test: Pulse Width  $\leq 300\mu s$ , Duty Cycle  $\leq 2\%$ .
4. Guaranteed by design, not subject to production
5. EAS condition:  $T_J=25^{\circ}\text{C}, V_{DD}=15V, V_G=10V, L=1\text{mH}, R_g=25\Omega$

## Test circuit

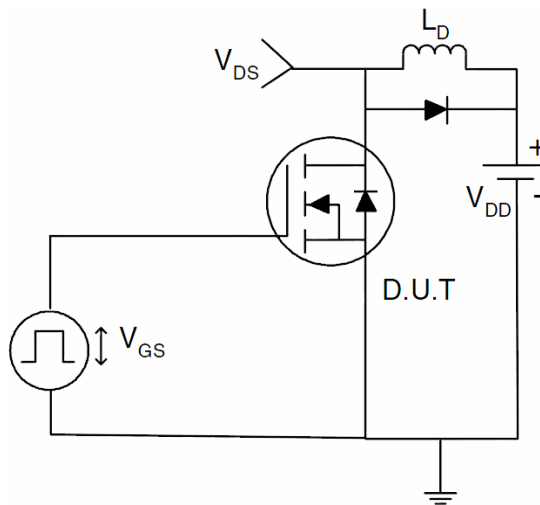
### 1) E<sub>AS</sub> test Circuits



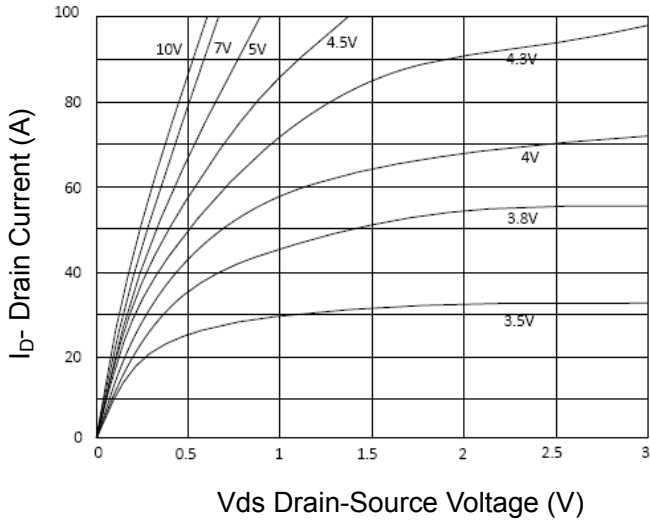
### 2) Gate charge test Circuit:



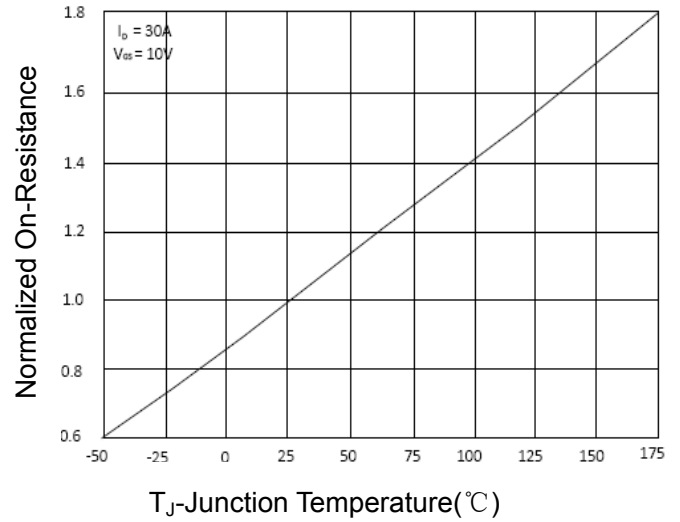
### 3) Switch Time Test Circuit:



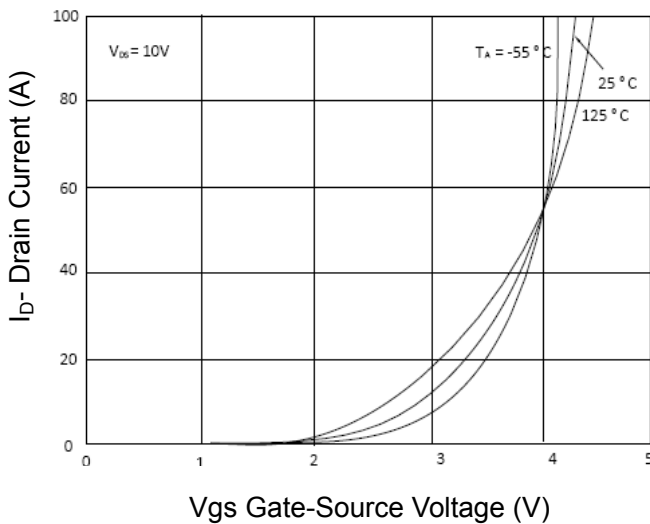
## TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS (Curves)



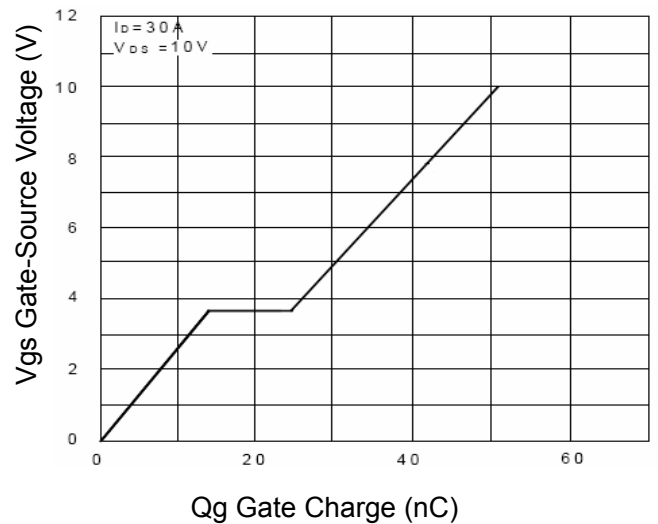
**Figure 1 Output Characteristics**



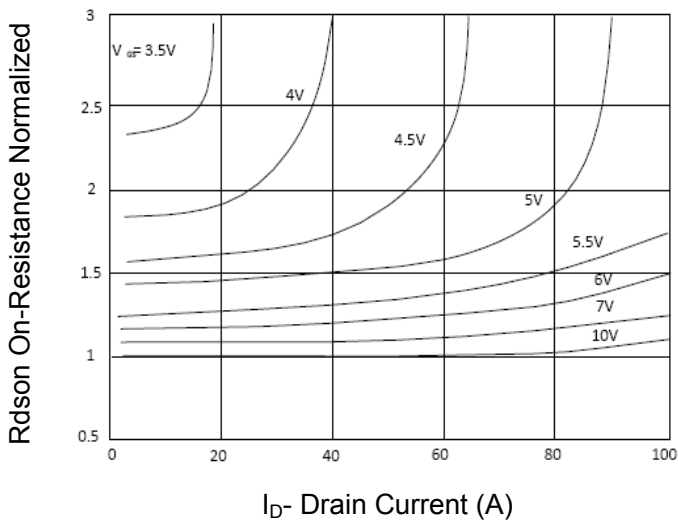
**Figure 4 Rdson-Junction Temperature**



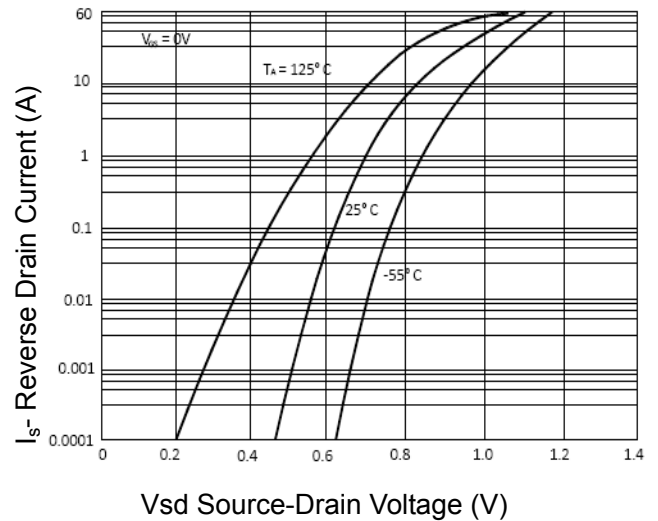
**Figure 2 Transfer Characteristics**



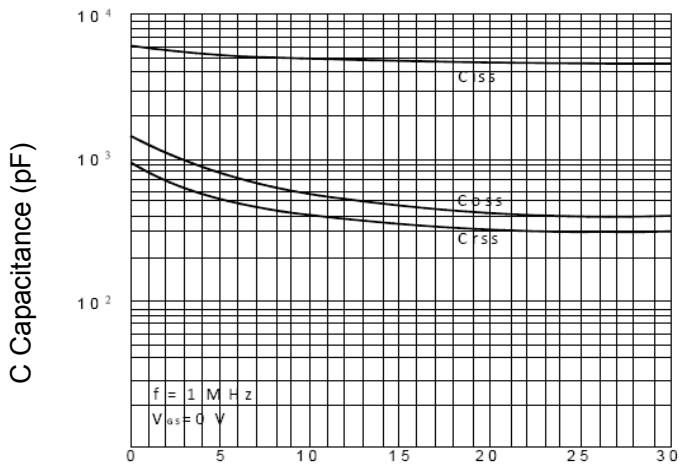
**Figure 5 Gate Charge**



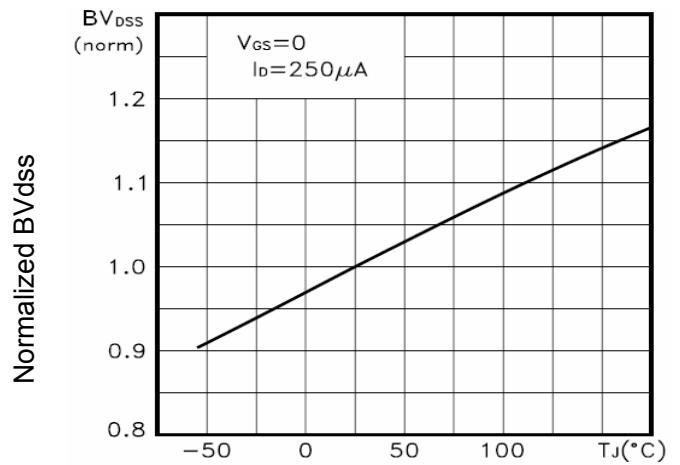
**Figure 3 Rdson- Drain Current**



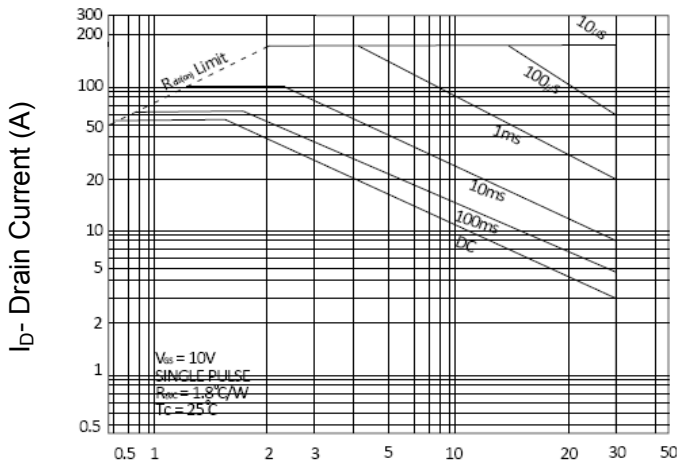
**Figure 6 Source- Drain Diode Forward**



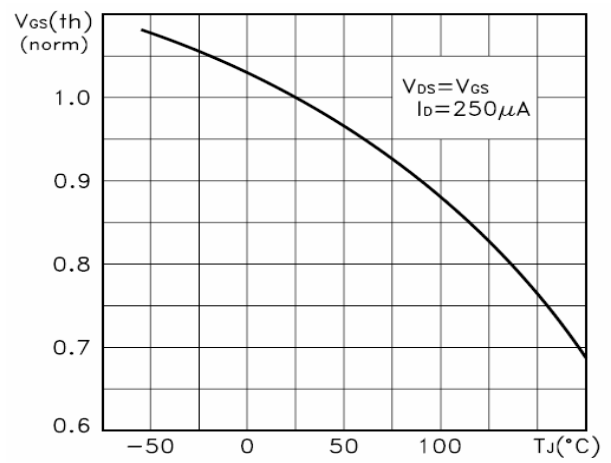
Vds Drain-Source Voltage (V)  
**Figure 7 Capacitance vs Vds**



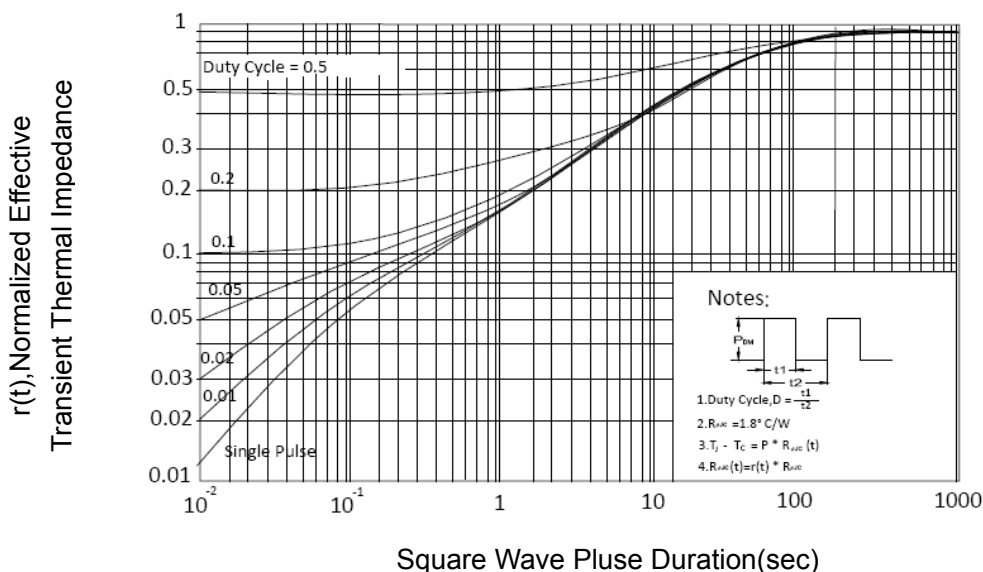
T<sub>J</sub>-Junction Temperature(°C)  
**Figure 9 BV<sub>DSS</sub> vs Junction Temperature**



Vds Drain-Source Voltage (V)  
**Figure 8 Safe Operation Area**

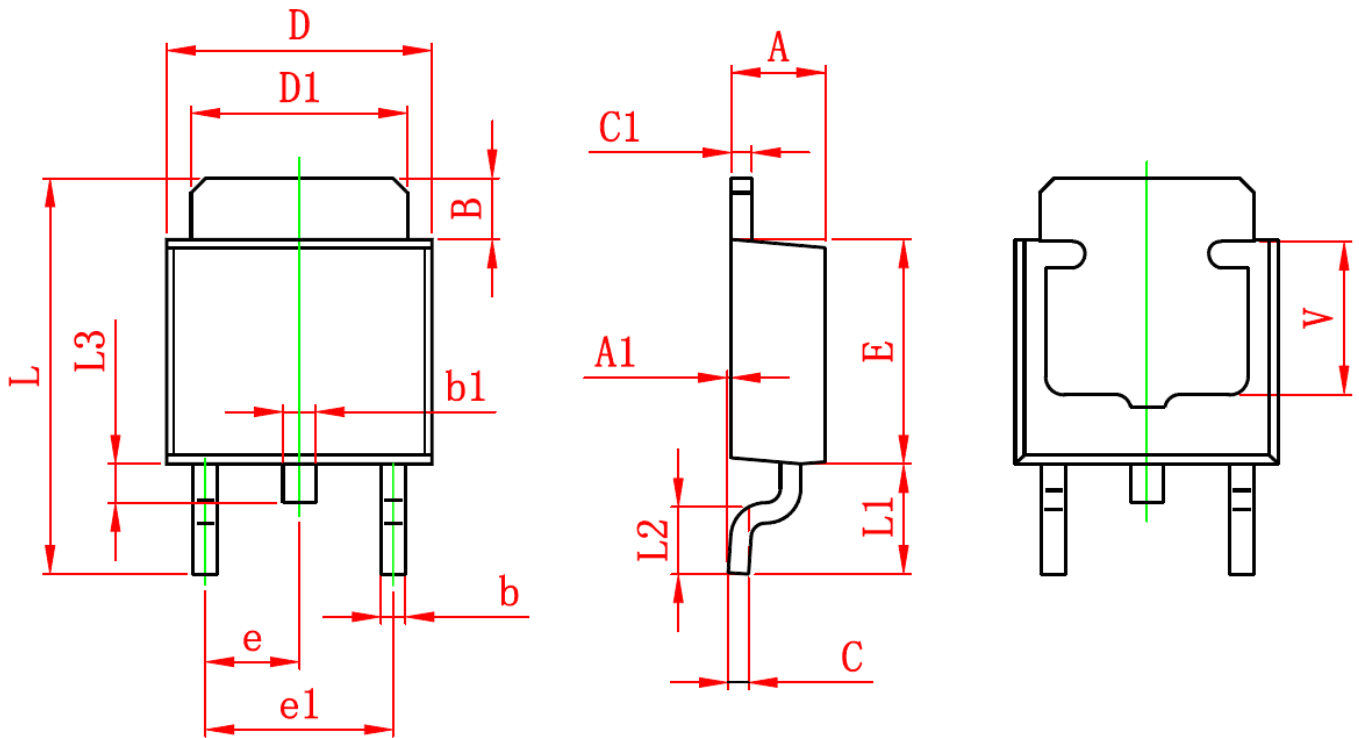


T<sub>J</sub>-Junction Temperature(°C)  
**Figure 10 V<sub>GS(th)</sub> vs Junction Temperature**



**Figure 11 Normalized Maximum Transient Thermal Impedance**

## TO-252-2L Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	2.200	2.400	0.087	0.094
A1	0.000	0.127	0.000	0.005
B	1.350	1.650	0.053	0.065
b	0.500	0.700	0.020	0.028
b1	0.700	0.900	0.028	0.035
c	0.430	0.580	0.017	0.023
c1	0.430	0.580	0.017	0.023
D	6.350	6.650	0.250	0.262
D1	5.200	5.400	0.205	0.213
E	5.400	5.700	0.213	0.224
e	2.300 TYP.		0.091 TYP.	
e1	4.500	4.700	0.177	0.185
L	9.500	9.900	0.374	0.390
L1	2.550	2.900	0.100	0.114
L2	1.400	1.780	0.055	0.070
L3	0.600	0.900	0.024	0.035
V	3.800 REF.		0.150 REF.	

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